FAIRCHILD
A Schlumberger Company

IRF350-353
N-channel Power MOSFETs, 15 A, 350 V/400 V

T-39-13

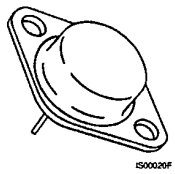
Power And Discrete Division

Description

These devices are n-channel, enhancement mode, power MOSFETs designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.

- **V_{GS} Rated at ±20 V**
- **Silicon Gate for Fast Switching Speeds**
- **I_{DSS}, $V_{DS(on)}$, SOA and $V_{GS(th)}$ Specified at Elevated Temperature**
- **Rugged**

TO-204AA



IS00020F

IRF350
IRF351
IRF352
IRF353

Maximum Ratings

Symbol	Characteristic	Rating IRF350/352	Rating IRF351/353	Unit
V_{DSS}	Drain to Source Voltage	400	350	V
V_{DGR}	Drain to Gate Voltage R_{GS} = 1.0 MΩ	400	350	V
V_{GS}	Gate to Source Voltage	±20	±20	V
T_J, T_{stg}	Operating Junction and Storage Temperatures	−55 to +150	−55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8″ From Case for 5 s	275	275	°C
Maximum On-State Characteristics				
		IRF350/351	**IRF352/353**	
$R_{DS(on)}$	Static Drain-to-Source On Resistance	0.3	0.4	Ω
I_D	Drain Current Continuous Pulsed	 15 60	 13 52	A
Maximum Thermal Characteristics				
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.83	0.83	°C/W
P_D	Total Power Dissipation at T_C = 25°C	150	150	W

Notes
For information concerning connection diagram and package outline, refer to Section 7.

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Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit	Test Conditions
Off Characteristics					
$V_{(BR)DSS}$	Drain Source Breakdown Voltage[1]			V	V_{GS} = 0 V, I_D = 250 μA
	IRF350/352	400			
	IRF351/353	350			
I_{DSS}	Zero Gate Voltage Drain Current		250	μA	V_{DS} = Rated V_{DSS}, V_{GS} = 0 V
			1000	μA	V_{DS} = 0.8 x Rated V_{DSS}, V_{GS} = 0 V, T_C = 125°C
I_{GSS}	Gate-Body Leakage Current		±100	nA	V_{GS} = ±20 V, V_{DS} = 0 V
On Characteristics					
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	V	I_D = 250 μA, V_{DS} = V_{GS}
$R_{DS(on)}$	Static Drain-Source On-Resistance[2]			Ω	V_{GS} = 10 V, I_D = 8.0 A
	IRF350/351		0.3		
	IRF352/353		0.4		
g_{fs}	Forward Transconductance	8.0		S (℧)	V_{DS} = 10 V, I_D = 8.0 A
Dynamic Characteristics					
C_{iss}	Input Capacitance		3000	pF	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz
C_{oss}	Output Capacitance		600	pF	
C_{rss}	Reverse Transfer Capacitance		200	pF	
Switching Characteristics (T_C = 25°C, *Figures 9, 10*)					
$t_{d(on)}$	Turn-On Delay Time		35	ns	V_{DD} = 180 V, I_D = 8.0 A, V_{GS} = 10 V, R_{GEN} = 4.7 Ω, R_{GS} = 4.7 Ω
t_r	Rise Time		65	ns	
$t_{d(off)}$	Turn-Off Delay Time		150	ns	
t_f	Fall Time		75	ns	
Q_g	Total Gate Charge		120	nC	V_{GS} = 10 V, I_D = 16 A, V_{DD} = 400 V

Symbol	Characteristic	Typ	Max	Unit	Test Conditions
Source-Drain Diode Characteristics					
V_{SD}	Diode Forward Voltage				
	IRF350/351		1.6	V	I_S = 15 A; V_{GS} = 0 V
	IRF352/353		1.5	V	I_S = 13 A; V_{GS} = 0 V
t_{rr}	Reverse Recovery Time	600		ns	I_S = 15 A; dI_S/dt = 100 A/μS

Notes
1. T_J = +25°C to +150°C
2. Pulse test: Pulse width ≤ 80 μs, Duty cycle ≤ 1%

Typical Performance Curves

Figure 1 Output Characteristics

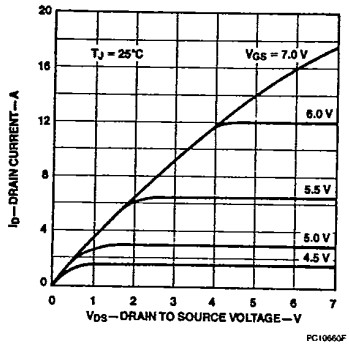


Figure 2 Static Drain to Source On Resistance vs Drain Current

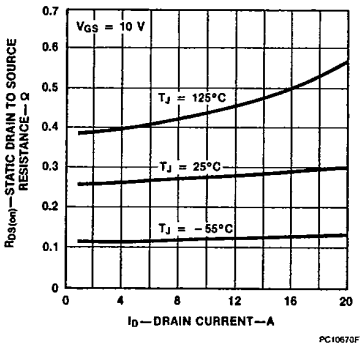


Figure 3 Transfer Characteristics

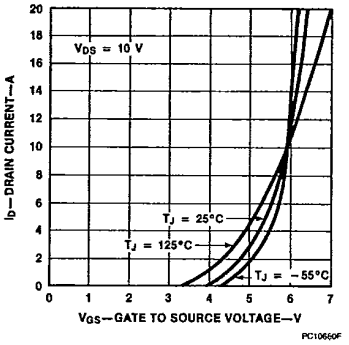


Figure 4 Temperature Variation of Gate to Source Threshold Voltage

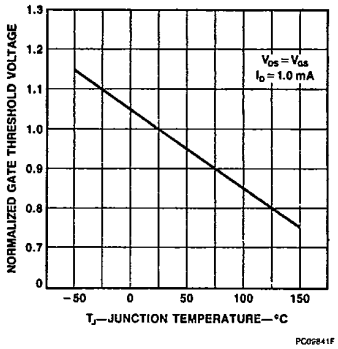


Figure 5 Capacitance vs Drain to Source Voltage

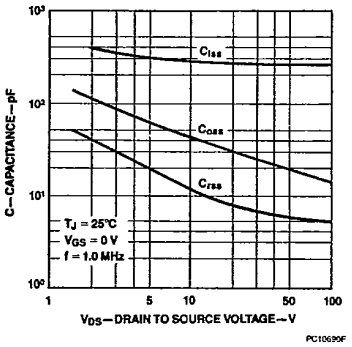
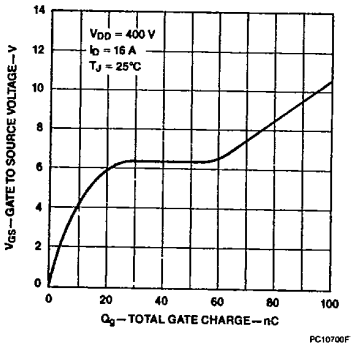


Figure 6 Gate to Source Voltage vs Total Gate Charge



Typical Performance Curves (Cont.)

Figure 7 Forward Biased Safe Operating Area

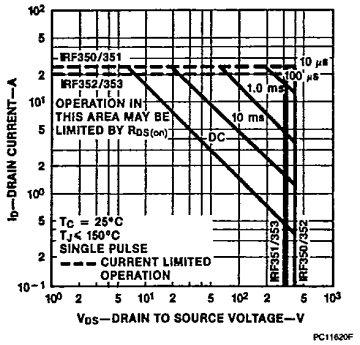
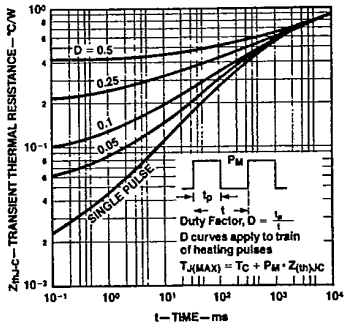


Figure 8 Transient Thermal Resistance vs Time



Typical Electrical Characteristics

Figure 9 Switching Test Circuit

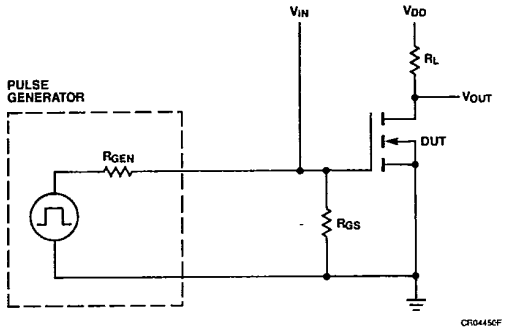


Figure 10 Switching Waveforms